

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

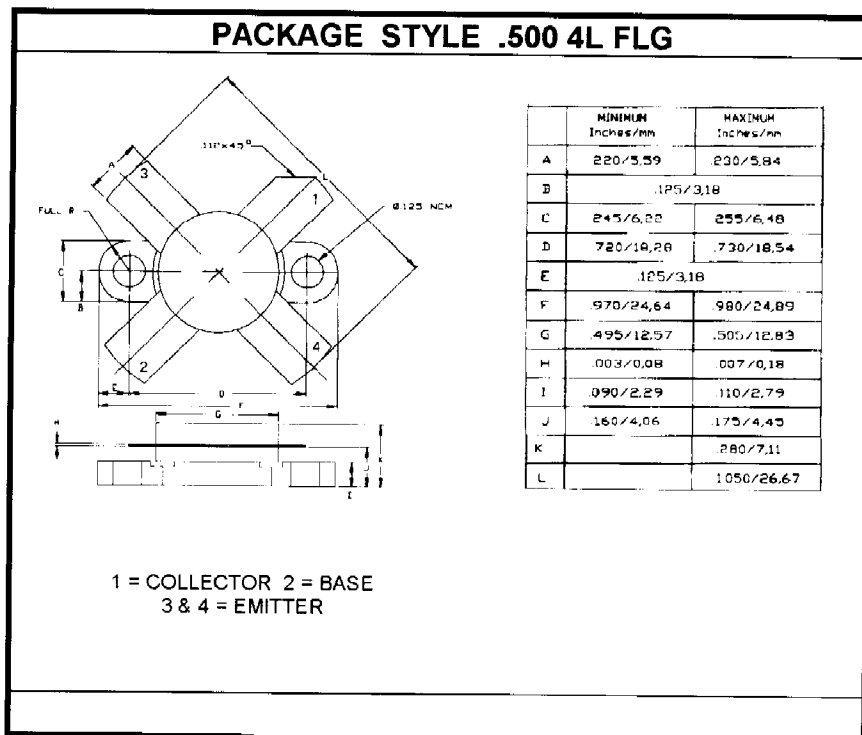
BLW50F is Designed for use in transmitters in the HF and VHF band applications up to 30 MHz.

FEATURES:

- $P_G = 14$ dB min. at 75 W/30 MHz
- $IMD_3 = 50$ dBc max. at 75 W(PEP)
- **Omnigold™** Metalization System

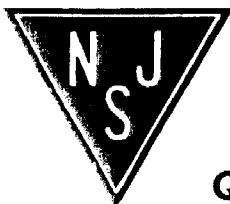
MAXIMUM RATINGS

I_C	3.25 A
V_{CBO}	110 V
V_{CEO}	55 V
V_{EBO}	4.0 V
P_{DISS}	87 W @ $T_C = 25^\circ C$
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	2.0 °C/W



CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	$I_C = 100$ mA	110			V
BV_{CE0}	$I_C = 200$ mA	55			V
BV_{EBO}	$I_E = 10$ mA	4.0			V
I_{CES}	$V_{CE} = 55$ V			10	mA
h_{FE}	$V_{CE} = 6.0$ V $I_C = 1.4$ A	19	---	50	---
C_{ob}	$V_{CB} = 50$ V $f = 1.0$ MHz			100	pF
G_p		14	---		dB
IMD_3	$V_{CE} = 50$ V $P_{OUT} = 75$ W(PEP)	---	---	-30	dBc
η_c		37			%



NJ Semi-Conductors reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However, NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.